# imall

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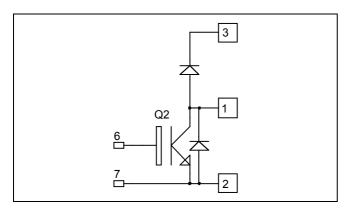
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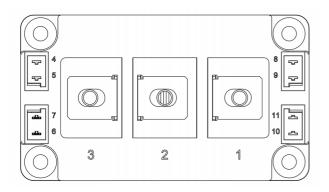
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#### Boost chopper Trench + Field Stop IGBT4 Power Module





# $V_{CES} = 1200V$

APTGL325DA120D3G

### $I_{\rm C} = 325 {\rm A}$ @ Tc = 80°C

#### Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

#### Features

- Trench + Field Stop IGBT 4 Technology
  - Low voltage drop
  - Low leakage current
  - Low switching losses
  - Soft recovery parallel diodes
  - Low diode VF
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- High level of integration
- M6 power connectors

#### Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T<sub>C</sub> of V<sub>CEsat</sub>
- RoHS Compliant

#### Absolute maximum ratings

Sy	mbol	Parameter		Max ratings	Unit
V	V <sub>CES</sub>	Collector - Emitter Breakdown Voltage		1200	V
I <sub>C</sub>	Continuous Collector Current	$T_C = 25^{\circ}C$	420		
	IC	Continuous Conector Current	$T_C = 80^{\circ}C$	325	Α
1	[ <sub>CM</sub>	Pulsed Collector Current	$T_C = 25^{\circ}C$	600	
V	V <sub>GE</sub>	Gate – Emitter Voltage		$\pm 20$	V
	P <sub>D</sub>	Maximum Power Dissipation	$T_C = 25^{\circ}C$	1500	W
RB	SOA	Reverse Bias Safe Operating Area	$T_j = 125^{\circ}C$	600A @ 1100V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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#### All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics								
Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit		
I <sub>CES</sub>	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				200	μA	
V	Collector Emitter saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		1.8	2.2	V	
V <sub>CE(sat)</sub>	Concetor Emitter saturation voltage	$I_{\rm C} = 300 {\rm A}$ $T_{\rm j} = 125^{\circ} {\rm C}$		2.2		v		
V <sub>GE(th)</sub>	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 11 \text{mA}$		5.0	5.8	6.5	V	
I <sub>GES</sub>	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA	

#### **Dynamic Characteristics**

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$ $f = 1MHz$			18.6		
Coes	Output Capacitance				1.16		nF
C <sub>res</sub>	Reverse Transfer Capacitance				1		
Q <sub>G</sub>	Gate charge	$V_{GE}$ = -8V / 15V ; $V_{CE}$ =600V I <sub>C</sub> =300A			1.7		μC
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = \pm 15V$ $V_{CE} = 600V$ $I_C = 300A$			200		ns
Tr	Rise Time				40		
T <sub>d(off)</sub>	Turn-off Delay Time				380		
T <sub>f</sub>	Fall Time	$R_{\rm G} = 1.5\Omega$			70		
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switch	hing (150°C)		220		
T <sub>r</sub>	Rise Time	$V_{GE} = \pm 15V$ $V_{CE} = 600V$			50		ns
T <sub>d(off)</sub>	Turn-off Delay Time	$I_{\rm C} = 300 {\rm A}$	01		450		
T <sub>f</sub>	Fall Time	$R_G = 1.5\Omega$			80		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{CE} = 600V$	$T_J = 150^{\circ}C$		27		mJ
E <sub>off</sub>	Turn-off Switching Energy	$I_{\rm C} = 300 \text{A}$ $R_{\rm G} = 1.5 \Omega$	$T_J = 150^{\circ}C$		29		mJ
I <sub>sc</sub>	Short Circuit data	$\begin{array}{l} V_{GE} \leq \!\! 15V \; ; \; V_{Bus} = 900V \\ t_p \leq \!\! 10\mu s \; ; \; T_j = 150^\circ C \end{array}$			1200		А

#### **Diode ratings and characteristics**

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V <sub>RRM</sub>	Maximum Repetitive Reverse Voltage			1200			V
I <sub>RRM</sub>	Maximum Reverse Leakage Current	V <sub>R</sub> =1200V	$T_j = 25^{\circ}C$ $T_i = 150^{\circ}C$			250 2000	μΑ
I <sub>F</sub>	DC Forward Current		$T_C = 80^{\circ}C$		300		А
V <sub>F</sub>	Diode Forward Voltage	$I_{\rm F} = 300 {\rm A}$ $V_{\rm GE} = 0 {\rm V}$	$T_j = 25^{\circ}C$		1.7	2.2	V
۷F			$T_{j} = 150^{\circ}C$		1.65		v
t	Reverse Recovery Time	$I_F = 300A$ $V_R = 600V$ $di/dt = 7000A/\mu s$	$T_j = 25^{\circ}C$		155		ns μC
t <sub>rr</sub>			$T_{j} = 150^{\circ}C$		300		
Q <sub>rr</sub>	Reverse Recovery Charge		$T_j = 25^{\circ}C$		29		
Qrr	Reverse Recovery charge		$T_{j} = 150^{\circ}C$		61		μυ
E <sub>rr</sub>	Reverse Recovery Energy		$T_j = 25^{\circ}C$		13		mJ
Lur			$T_{j} = 150^{\circ}C$		24		1115

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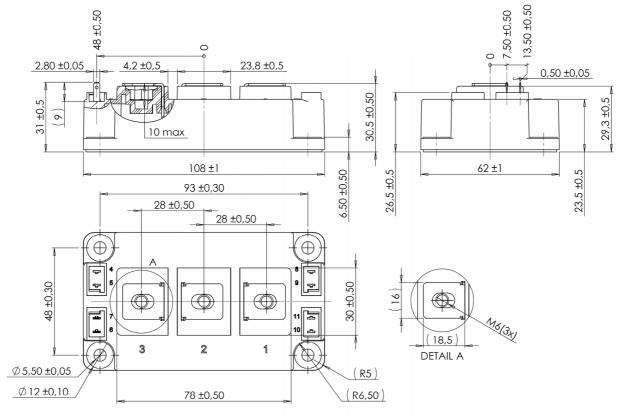


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#### Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
D	Junction to Case Thermal Resistance IGBT Diode		IGBT			0.10	°C/W
R <sub>thJC</sub>			Diode			0.17	
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T <sub>J</sub>	Operating junction temperature range		-40		175		
T <sub>STG</sub>	Storage Temperature Range			-40		125	°C
T <sub>C</sub>	Operating Case Temperature			-40		125	
Torque	Mounting torque	For terminals	M6	3		5	N.m
Torque		To Heatsink	M6	3		5	19.111
Wt	Package Weight					350	g

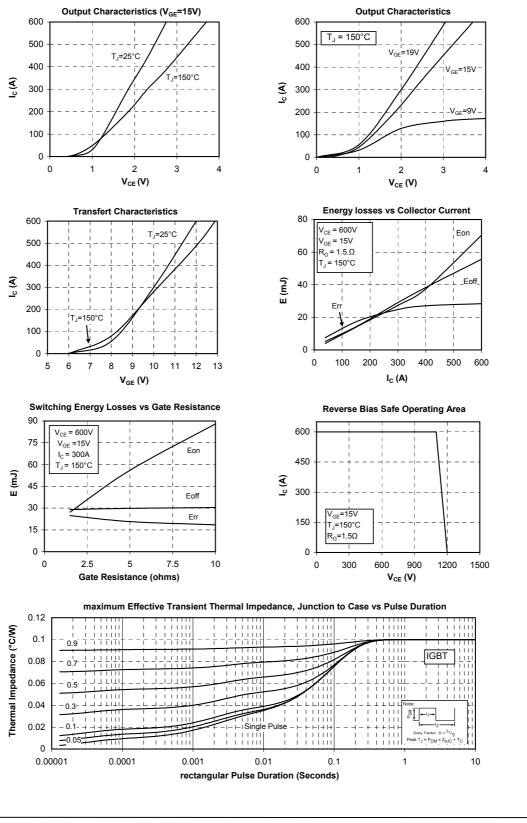
#### D3 Package outline (dimensions in mm)



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#### **Typical Performance Curve**

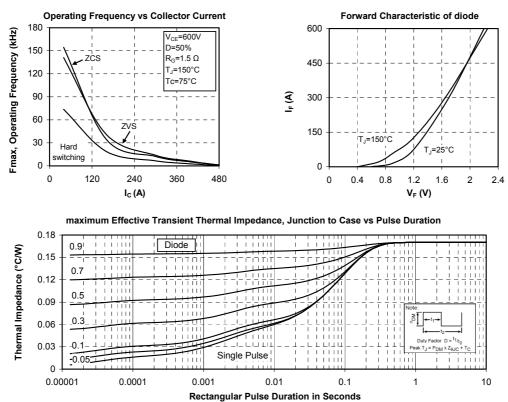


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